

20V N-CHANNEL ENHANCEMENT MODE MOSFET

SUMMARY

 $V_{(BR)DSS} = 20V; R_{DS(ON)} = 0.02\Omega; I_D = 10.2A$

DESCRIPTION

This new generation of TRENCH MOSFETs from Zetex utilizes a unique structure that combines the benefits of low on-resistance with fast switching speed. This makes them ideal for high efficiency, low voltage, power management applications.

FEATURES

- Low on-resistance
- Fast switching speed
- · Low threshold
- Low gate drive
- Low profile SOIC package

APPLICATIONS

- Disconnect switches
- Motor control

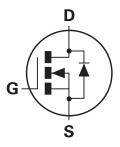
ORDERING INFORMATION

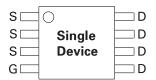
DEVICE	REEL SIZE	TAPE WIDTH	QUANTITY PER REEL
ZXMN2A02N8TA	7″	12mm	500 units
ZXMN2A02N8TC	13″	12mm	2500 units

DEVICE MARKING

ZXMN 2A02

SO8





Top View



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ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	LIMIT	UNIT
Drain-Source Voltage	V _{DSS}	20	V
Gate Source Voltage	V _{GS}	±12	V
Continuous Drain Current V _{GS} =10V; T _A =25°C $^{(b)}$ V _{GS} =10V; T _A =70°C $^{(b)}$ V _{GS} =10V; T _A =25°C $^{(a)}$	ID	10.2 8.2 8.3	A
Pulsed Drain Current ^(c)	I _{DM}	50	А
Continuous Source Current (Body Diode) ^(b)	I _S	4.3	А
Pulsed Source Current (Body Diode) ^(c)	I _{SM}	50	А
Power Dissipation at T _A =25°C ^(a) Linear Derating Factor	P _D	1.56 12.5	W mW/°C
Power Dissipation at T _A =25°C ^(b) Linear Derating Factor	P _D	2.5 20	W mW/°C
Operating and Storage Temperature Range	T _j :T _{stg}	-55 to 150	°C

THERMAL RESISTANCE

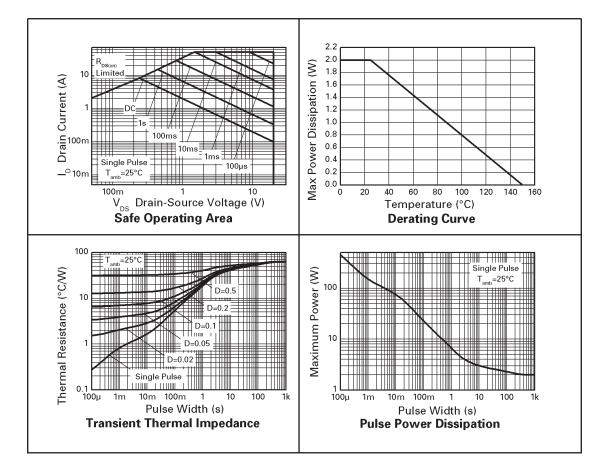
PARAMETER	SYMBOL	VALUE	UNIT
Junction to Ambient ^(a)	$R_{\theta JA}$	80	°C/W
Junction to Ambient ^(b)	$R_{\theta JA}$	50	°C/W

NOTES

(a) For a device surface mounted on 25mm x 25mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions (b) For a device surface mounted on FR4 PCB measured at t \leq 10 secs.

(c) Repetitive rating 25mm x 25mm FR4 PCB, D = 0.02, pulse width 300μ s - pulse width limited by maximum junction temperature.





CHARACTERISTICS



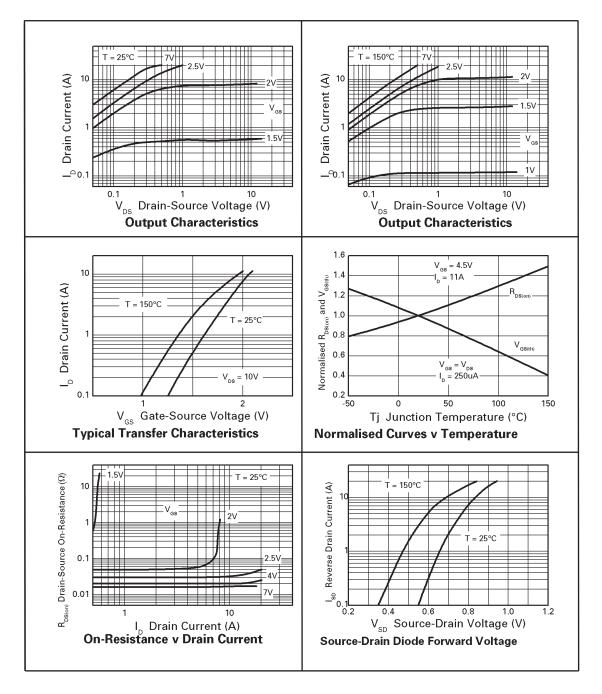
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PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.	
STATIC						-	
Drain-Source Breakdown Voltage	V(BR)DSS	20			V	I _D =250μA, V _{GS} =0V	
Zero Gate Voltage Drain Current	IDSS			1	μA	V _{DS} =20V, V _{GS} =0V	
Gate-Body Leakage	IGSS			100	nA	$V_{GS}=\pm 12V, V_{DS}=0V$	
Gate-Source Threshold Voltage	V _{GS(th)}	0.7			V	I _D =250μA, V _{DS} = V _{GS}	
Static Drain-Source On-State	R _{DS(on)}			0.02	Ω	V _{GS} =4.5V, I _D =11A	
Resistance ⁽¹⁾				0.04	Ω	V _{GS} =2.5V, I _D =8.4A	
Forward Transconductance ⁽¹⁾⁽³⁾	g _{fs}		27		S	V _{DS} =10V,I _D =11A	
DYNAMIC ⁽³⁾							
Input Capacitance	Ciss		1900		pF		
Output Capacitance	Coss		356		pF	V _{DS} =10V, V _{GS} =0V, f=1MHz	
Reverse Transfer Capacitance	C _{rss}		218		pF		
SWITCHING ^{(2) (3)}							
Turn-On Delay Time	^t d(on)		7.9		ns		
Rise Time	tr		10		ns	V _{DD} =10V, I _D =1A	
Turn-Off Delay Time	^t d(off)		33.3		ns	R _G ≅6.0Ω, V _{GS} =4.5V	
Fall Time	tf		13.6		ns		
Total Gate Charge	Qg		18.9		nC		
Gate-Source Charge	Qgs		5.2		nC	V _{DS} =10V,V _{GS} =4.5V, I _D =11A	
Gate-Drain Charge	Q _{gd}		4.9		nC		
SOURCE-DRAIN DIODE							
Diode Forward Voltage ⁽¹⁾	V _{SD}		0.85	0.95	V	TJ=25°C, IS=11.5A,	
						V _{GS} =0V	
Reverse Recovery Time ⁽³⁾	t _{rr}		16.3		ns	Т _Ј =25°С, I _F =2.1А,	
Reverse Recovery Charge ⁽³⁾	Qrr		7.8		nC	di/dt= 100A/µs	

ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}C$ unless otherwise stated).

NOTES

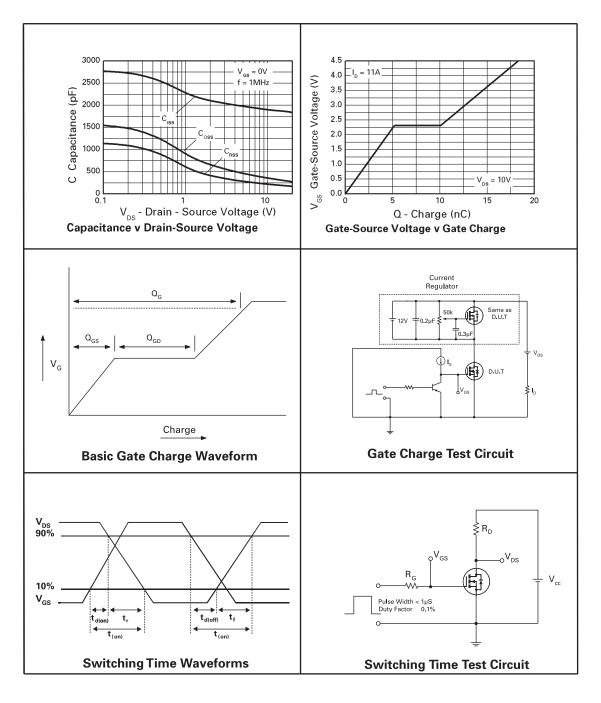
(1) Measured under pulsed conditions. Width ≤300µs. Duty cycle ≤ 2%.
(2) Switching characteristics are independent of operating junction temperature.
(3) For design aid only, not subject to production testing.





CHARACTERISTICS





CHARACTERISTICS



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or

2. support or sustain life and whose failure to perform when properly used in accordance with instructions

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Product status key:

"Preview"Future device intended for production at some point. Samples may be available

"Active"Product status recommended for new designs

"Last time buy (LTB)"Device will be discontinued and last time buy period and delivery is in effect

"Not recommended for new designs"Device is still in production to support existing designs and production

"Obsolete"Production has been discontinued

Datasheet status key:

"Draft version"This term denotes a very early datasheet version and contains highly provisional

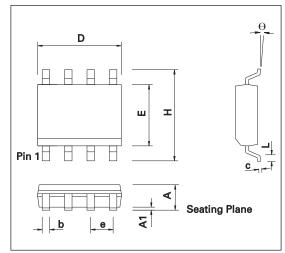
information, which may change in any manner without notice.

"Provisional version"This term denotes a pre-release datasheet. It provides a clear indication of anticipated performance. However, changes to the test conditions and specifications may occur, at any time and without notice.

"Issue"This term denotes an issued datasheet containing finalized specifications. However, changes to specifications may occur, at any time and without notice.



PACKAGE OUTLINE



CONTROLLING DIMENSIONS ARE IN INCHES APPROX IN MILLIMETERS

DIM	INC	HES	MILLIM	IMETRES	
	MIN	MAX	MIN	MAX	
А	0.053	0.069	1.35	1.75	
A1	0.004	0.010	0.10	0.25	
D	0.189	0.197	4.80	5.00	
н	0.228	0.244	5.80	6.20	
E	0.150	0.157	3.80	4.00	
L	0.016	0.050	0.40	1.27	
е	0.050	BSC	1.27 BSC		
b	0.013	0.020	0.33	0.51	
с	0.008	0.010	0.19	0.25	
θ	0°	8°	0°	8°	
h	0.010	0.020	0.25	0.50	

PACKAGE DIMENSIONS

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